



ATTORNEY DOCKET NO.: S.A. LYTLE 18

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Steven A. Lytle
Serial No.: 09/667,046
Filed: September 21, 2000
Title: DUAL DAMASCENE PROCESS WITH NO
PASSING METAL FEATURES
Grp./A.U.: 2811
Examiner: Hung K. Vu

Commissioner for Patents
Washington, D. C. 20231

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on

07/16/2002 (Date)

Stephanie Puth (Printed or typed name of person signing the certificate)

Stephanie Puth (Signature of the person signing the certificate)

Sir:

PRELIMINARY AMENDMENT

Before examination of the above-identified application, please amend it as follows:

IN THE CLAIMS:

(1) Please amend Claim 21 as follows:

21. (Twice Amended) A semiconductor device, comprising:

a first metal feature located over a semiconductor surface and having a first etch stop layer
and a first interlevel dielectric layer located thereover and a second etch stop layer and a second
interlevel dielectric layer located over the first etch stop layer and the first interlevel dielectric layer;